Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-33. (Canceled)

34. (New) A semiconductor device comprising:

a semiconductor film having a polycrystal structure with a composition ratio of germanium to silicon being 0.1 atomic percent or more and 10 atomic percent or below; and

a wiring adjacent to the semiconductor film,

wherein {101} planes in the semiconductor film reach 30% or more of all lattice planes detected by electron backscatter diffraction.

35. (New) A semiconductor device comprising:

a semiconductor film having a polycrystal structure with a composition ratio of germanium to silicon being 0.1 atomic percent or more and 10 atomic percent or below; and

a wiring adjacent to the semiconductor film,

wherein {101} planes in the semiconductor film reach 30% or more of all lattice planes detected by electron backscatter diffraction; and

wherein the semiconductor film comprises:

nitrogen with a concentration less than 5×10^{18} atoms/cm^3,

carbon with a concentration less than 5×10^{18} atoms/cm^3, and

oxygen with a concentration less than 1×10^{19} atoms/cm^3.

36. (New) A semiconductor device comprising:

a semiconductor film having a polycrystal structure with a composition ratio of germanium to silicon being 0.1 atomic percent or more and 10 atomic percent or below; and

a wiring adjacent to the semiconductor film,

wherein {101} planes in the semiconductor film reach 30% or more of all lattice planes detected by electron backscatter diffraction; and

wherein the semiconductor film is obtained by crystallizing an amorphous semiconductor film formed by intermittent electric discharge while setting a repetition frequency to 10 kHz or below and a duty ratio to 50% or below.

37. (New) A semiconductor device comprising:

a semiconductor film having a polycrystal structure with a composition ratio of germanium to silicon being 0.1 atomic percent or more and 10 atomic percent or below; and

a wiring adjacent to the semiconductor film,

wherein {101} planes in the semiconductor film reach 30% or more of all lattice planes detected by electron backscatter diffraction;

wherein the semiconductor film comprises:

nitrogen with a concentration less than 5×10^{18} atoms/cm^3;

carbon with a concentration less than 5×10^{18} atoms/cm^3; and

oxygen with a concentration less than 1×10^{19} atoms/cm^3,

wherein the semiconductor film is obtained by crystallizing an amorphous semiconductor film formed by intermittent electric discharge while setting a repetition frequency to 10 kHz or below and a duty ratio to 50% or below.

38. (New) A semiconductor device according to claim 34, wherein a thickness of the semiconductor film is in a range from 10 nm through 100 nm.

39. (New) A semiconductor device according to claim 35, wherein a thickness of the semiconductor film is in a range from 10 nm through 100 nm.

40. (New) A semiconductor device according to claim 36, wherein a thickness of the semiconductor film is in a range from 10 nm through 100 nm.

41. (New) A semiconductor device according to claim 37, wherein a thickness of the semiconductor film is in a range from 10 nm through 100 nm.

42. (New) A semiconductor device according to claim 34, wherein the semiconductor film forms a channel formation region.

43. (New) A semiconductor device according to claim 35, wherein the semiconductor film forms a channel formation region.

44. (New) A semiconductor device according to claim 36, wherein the semiconductor film forms a channel formation region.

45. (New) A semiconductor device according to claim 37, wherein the semiconductor film forms a channel formation region.

46. (New) A semiconductor device according to claim 34, wherein the semiconductor device is an EL display device.

47. (New) A semiconductor device according to claim 35, wherein the semiconductor device is an EL display device.

48. (New) A semiconductor device according to claim 36, wherein the semiconductor device is an EL display device.

49. (New) A semiconductor device according to claim 37, wherein the semiconductor device is an EL display device.

50. (New) A portable data terminal comprising:

a semiconductor film having a polycrystal structure with a composition ratio of germanium to silicon being 0.1 atomic percent or more and 10 atomic percent or below; and

a wiring adjacent to the semiconductor film,

wherein {101} planes in the semiconductor film reach 30% or more of all lattice planes detected by electron backscatter diffraction.

51. (New) A video camera comprising:

a semiconductor film having a polycrystal structure with a composition ratio of germanium to silicon being 0.1 atomic percent or more and 10 atomic percent or below; and

a wiring adjacent to the semiconductor film,

wherein {101} planes in the semiconductor film reach 30% or more of all lattice planes detected by electron backscatter diffraction.

52. (New) A still camera comprising:

a semiconductor film having a polycrystal structure with a composition ratio of germanium to silicon being 0.1 atomic percent or more and 10 atomic percent or below; and

a wiring adjacent to the semiconductor film,

wherein {101} planes in the semiconductor film reach 30% or more of all lattice planes detected by electron backscatter diffraction.

53. (New) A personal computer comprising:

a semiconductor film having a polycrystal structure with a composition ratio of germanium to silicon being 0.1 atomic percent or more and 10 atomic percent or below; and

a wiring adjacent to the semiconductor film,

wherein {101} planes in the semiconductor film reach 30% or more of all lattice planes detected by electron backscatter diffraction.

54. (New) A television comprising:

a semiconductor film having a polycrystal structure with a composition ratio of germanium to silicon being 0.1 atomic percent or more and 10 atomic percent or below; and

a wiring adjacent to the semiconductor film,

wherein {101} planes in the semiconductor film reach 30% or more of all lattice planes detected by electron backscatter diffraction.

55. (New) A projector comprising:

a semiconductor film having a polycrystal structure with a composition ratio of germanium to silicon being 0.1 atomic percent or more and 10 atomic percent or below; and

a wiring adjacent to the semiconductor film,

wherein {101} planes in the semiconductor film reach 30% or more of all lattice planes detected by electron backscatter diffraction.

56. (New) A portable data terminal according to claim 50,

wherein the semiconductor film comprises:

nitrogen with a concentration less than 5×10^{18} atoms/cm^3,

carbon with a concentration less than 5×10^{18} atoms/cm^3, and

oxygen with a concentration less than 1×10^{19} atoms/cm^3.

57. (New) A video camera according to claim 51,

wherein the semiconductor film comprises:

nitrogen with a concentration less than 5×10^{18} atoms/cm^3,

carbon with a concentration less than 5×10^{18} atoms/cm^3, and

oxygen with a concentration less than 1×10^{19} atoms/cm^3.

58. (New) A still camera according to claim 52,

wherein the semiconductor film comprises:

nitrogen with a concentration less than 5 x 10^{18} atoms/cm^3,

carbon with a concentration less than 5 x 10^{18} atoms/cm^3, and

oxygen with a concentration less than 1 x10^{19} atoms/cm^3.

59. (New) A personal computer according to claim 53,

wherein the semiconductor film comprises:

nitrogen with a concentration less than 5 x 10^{18} atoms/cm^3,

carbon with a concentration less than 5 x 10^{18} atoms/cm^3, and

oxygen with a concentration less than 1 x10^{19} atoms/cm^3.

60. (New) A television according to claim 54,

wherein the semiconductor film comprises:

nitrogen with a concentration less than 5 x 10^{18} atoms/cm^3,

carbon with a concentration less than 5 x 10^{18} atoms/cm^3, and

oxygen with a concentration less than 1 x10^{19} atoms/cm^3.

61. (New) A projector according to claim 55,

wherein the semiconductor film comprises:

nitrogen with a concentration less than 5 x 10^{18} atoms/cm^3,

carbon with a concentration less than 5 x 10^{18} atoms/cm^3, and

oxygen with a concentration less than 1 x10^{19} atoms/cm^3.

62. (New) A portable data terminal according to claim 50,

wherein the semiconductor film is obtained by crystallizing an amorphous semiconductor film formed by intermittent electric discharge while setting a repetition frequency to 10 kHz or below and a duty ratio to 50% or below.

63. (New) A video camera according to claim 51,

wherein the semiconductor film is obtained by crystallizing an amorphous semiconductor film formed by intermittent electric discharge while setting a repetition frequency to 10 kHz or below and a duty ratio to 50% or below.

64. (New) A still camera according to claim 52,

wherein the semiconductor film is obtained by crystallizing an amorphous semiconductor film formed by intermittent electric discharge while setting a repetition frequency to 10 kHz or below and a duty ratio to 50% or below.

65. (New) A personal computer according to claim 53,

wherein the semiconductor film is obtained by crystallizing an amorphous semiconductor film formed by intermittent electric discharge while setting a repetition frequency to 10 kHz or below and a duty ratio to 50% or below.

66. (New) A television according to claim 54,

wherein the semiconductor film is obtained by crystallizing an amorphous semiconductor film formed by intermittent electric discharge while setting a repetition frequency to 10 kHz or below and a duty ratio to 50% or below.

67. (New) A projector according to claim 55,

wherein the semiconductor film is obtained by crystallizing an amorphous semiconductor film formed by intermittent electric discharge while setting a repetition frequency to 10 kHz or below and a duty ratio to 50% or below.